

CFSH2-4L

SURFACE MOUNT SILICON SCHOTTKY DIODE



www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CFSH2-4L is a high quality Schottky Diode designed for applications where ultra small size and power dissipation are prime requirements. Packaged in a Tiny Leadless Package™ (TLP™), this component provides performance characteristics suitable for the most demanding size constrained applications.

TLPTM
Tiny Leadless
Package



Top View Bottom View

SOD-882L CASE

APPLICATIONS:

- DC / DC Converters
- Voltage Clamping
- Protection Circuits
- Battery powered devices including Cell Phones, Digital Cameras, Pagers, PDAs, Laptop Computers, etc.

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage

SYMBOL		UNITS
V_{RRM}	40	V
I_O	200	mA
I_{FSM}	1.0	A
P_D	100	mW
T_J	-65 to +125	°C
T_{stg}	-65 to +150	°C
Θ_{JA}	1000	°C/W

Average Forward Current

Peak Forward Surge Current, $t_p=8.3\text{ms}$

Power Dissipation

Operating Junction Temperature

Storage Temperature

Thermal Resistance

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

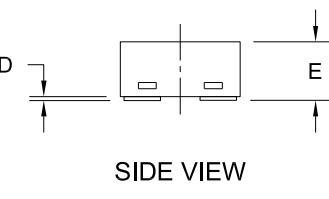
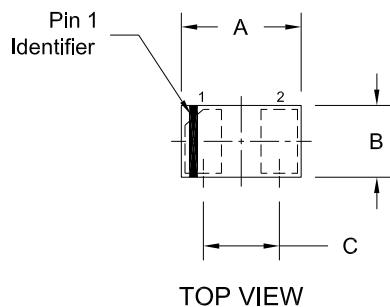
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=10\text{V}$		0.08	1.0	µA
I_R	$V_R=40\text{V}$		0.35	2.0	µA
BV_R	$I_R=10\mu\text{A}$	40			V
V_F	$I_F=10\text{mA}$		0.33	0.45	V
V_F	$I_F=100\text{mA}$			0.52	V
V_F	$I_F=200\text{mA}$		0.53	0.60	V
C_T	$V_R=4.0\text{V}, f=1.0\text{MHz}$		7.0	10	pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$		5.0		ns

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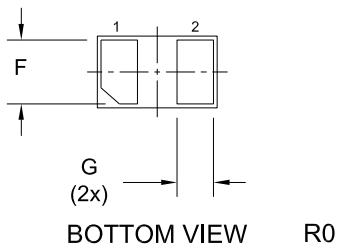
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SOD-882L CASE - MECHANICAL OUTLINE



SIDE VIEW



BOTTOM VIEW R0

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.041	0.95	1.05
B	0.022	0.026	0.55	0.65
C	0.026		0.65	
D	0.000	0.002	0.00	0.05
E	0.012	0.016	0.30	0.40
F	0.018	0.022	0.45	0.55
G	0.008	0.012	0.20	0.30

SOD-882L (REV:R0)

LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: N

R3 (10-December 2010)